

**MAGNETIC RANDOM ACCESS MEMORY (MRAM) CELLS HAVING  
SPLIT SUB-DIGIT LINES**

**Abstract of the Disclosure**

Magnetic random access memory cells having split sub-digit lines include a pair of sub-digit lines disposed over a semiconductor substrate. The pair of sub-digit lines are spaced apart from each other when viewed from a top plan view. A  
5 magnetic resistor is disposed over the pair of sub-digit lines. The magnetic resistor is disposed to overlap with the pair of sub-digit lines. The magnetic resistor is electrically connected to a predetermined region of the semiconductor substrate through a magnetic resistor contact hole that penetrates a gap region between the pair of sub-digit lines.